

a gate electrode controlling a flow of said carriers through said channel layer from said first ohmic electrode to said second ohmic electrode,

AS  
CONT. said gate electrode including an insulating metal oxide film formed at an interface to a surface of said semiconductor layer,

said metal oxide film being formed of a metal oxide of an element excluding an element constituting said compound semiconductor layer, said metal oxide having a free energy of formation larger than the absolute value of a free energy of formation of an oxide of an element constituting said semiconductor layer.

Please add new Claim 10, as follows:

sub B2  
AL 10. (NEW) A compound semiconductor device, comprising:

a compound semiconductor layer including a channel region;

a gate electrode electrically contacting said compound semiconductor layer, said gate electrode having a multi-layer structure including a Ti layer, a Pt layer and an Au layer; and

an intermediate layer including  $\text{TiO}_2$  provided between said Ti layer and said compound semiconductor layer.